BONDED WAFER AND METHOD FOR PRODUCING BONDED WAFER

ABSTRACT OF THE DISCLOSURE

A bonded wafer is produced by directly bonding a silicon wafer for active layer and a silicon wafer for support substrate without an insulating film and thinning the silicon wafer for active layer to a given thickness, in which a silicon wafer cut out from an ingot at a cutting angle of 0-0.1° (compound angle) with respect to a predetermined crystal face is used in each of the silicon wafer for active layer and silicon wafer for support substrate.

FIG. 1